

# HiPerFET™ Power MOSFETs Q-CLASS

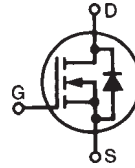
Single MOSFET Die

N-Channel Enhancement Mode  
Avalanche Rated, Low Q<sub>g</sub>,  
High dV/dt, Low t<sub>rr</sub>

**IXFK 21N100Q**  
**IXFX 21N100Q**

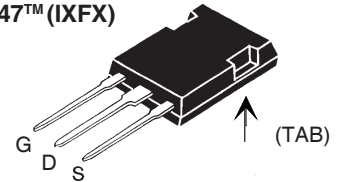
**V<sub>DSS</sub> = 1000 V**  
**I<sub>D25</sub> = 21 A**  
**R<sub>DS(on)</sub> = 0.50 Ω**

**t<sub>rr</sub> ≤ 250 ns**

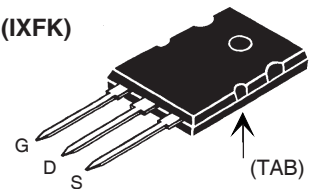


Symbol	Test Conditions	Maximum Ratings	
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 150°C	1000	V
V <sub>DGR</sub>	T <sub>J</sub> = 25°C to 150°C; R <sub>GS</sub> = 1 MΩ	1000	V
V <sub>GS</sub>	Continuous	±20	V
V <sub>GSM</sub>	Transient	±30	V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	21	A
I <sub>DM</sub>	T <sub>C</sub> = 25°C, pulse width limited by T <sub>JM</sub>	84	A
I <sub>AR</sub>	T <sub>C</sub> = 25°C	21	A
E <sub>AR</sub>	T <sub>C</sub> = 25°C	60	mJ
E <sub>AS</sub>	T <sub>C</sub> = 25°C	2.5	J
dv/dt	I <sub>S</sub> ≤ I <sub>DM</sub> , di/dt ≤ 100 A/μs, V <sub>DD</sub> ≤ V <sub>DSS</sub> T <sub>J</sub> ≤ 150°C, R <sub>G</sub> = 2 Ω	10	V/ns
P <sub>D</sub>	T <sub>C</sub> = 25°C	500	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
T <sub>L</sub>	1.6 mm (0.063 in.) from case for 10 s	300	°C
M <sub>d</sub>	Mounting torque	TO-264	0.4/6 Nm/lb.in.
Weight		PLUS 247	6 g
		TO-264	10 g

PLUS247™ (IXFX)



TO-264 AA (IXFK)



G = Gate  
S = Source

D = Drain  
TAB = Drain

### Features

- IXYS advanced low Q<sub>g</sub> process
- Low gate charge and capacitances
  - easier to drive
  - faster switching
- International standard packages
- Low R<sub>DS(on)</sub>
- Rated for unclamped Inductive load switching (UIS) rated
- Molding epoxies meet UL 94 V-0 flammability classification

### Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls

### Advantages

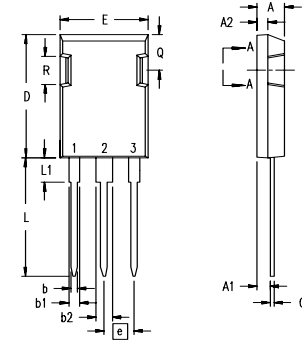
- PLUS 247™ package for clip or spring mounting
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values (T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
V <sub>DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1 mA	1000		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 4 mA	3		V
I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0			±100 nA
I <sub>DSS</sub>	V <sub>DS</sub> = V <sub>DSS</sub> V <sub>GS</sub> = 0 V T <sub>J</sub> = 125°C			100 μA
				2 mA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> Note 1			0.50 Ω

Symbol	Test Conditions	Characteristic Values		
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$		
		min.	typ.	max.
$g_{fs}$	$V_{DS} = 20\text{ V}; I_D = 0.5 \cdot I_{D25}$ Note 1	16	22	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		6900	pF
$C_{oss}$			550	pF
$C_{rss}$			90	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\ \Omega$ (External),		21	ns
$t_r$			18	ns
$t_{d(off)}$			60	ns
$t_f$			12	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		170	nC
$Q_{gs}$			38	nC
$Q_{gd}$			75	nC
$R_{thJC}$			0.26	K/W
$R_{thCK}$		0.15		K/W

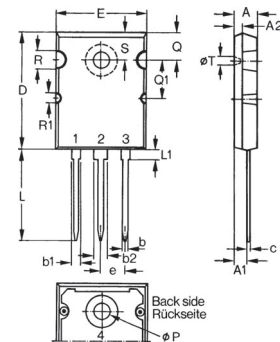
Source-Drain Diode		Characteristic Values		
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$		
Symbol	Test Conditions	min.	typ.	max.
$I_S$	$V_{GS} = 0\text{ V}$			21 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$			84 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}, \text{ Note 1}$			1.5 V
$t_{rr}$	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$			250 ns
$Q_{RM}$			1.4	$\mu\text{C}$
$I_{RM}$				8 A

Note: 1. Pulse test,  $t \leq 300\ \mu\text{s}$ , duty cycle  $d \leq 2\%$

**PLUS 247™ Outline**


Terminals: 1 - Gate  
2 - Drain (Collector)  
3 - Source (Emitter)  
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A <sub>1</sub>	2.29	2.54	.090	.100
A <sub>2</sub>	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b <sub>1</sub>	1.91	2.13	.075	.084
b <sub>2</sub>	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

**TO-264 AA Outline**


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

IXYS reserves the right to change limits, test conditions, and dimensions.

Fig. 1. Output Characteristics at 25°C

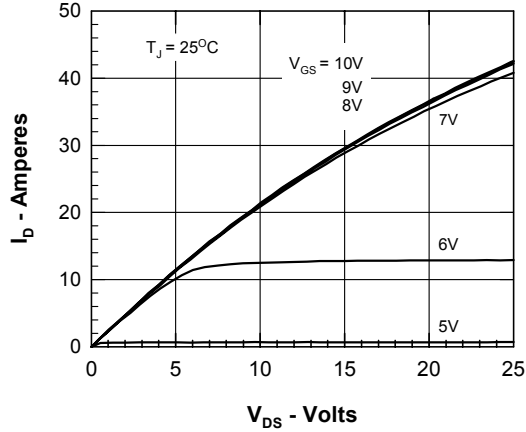


Fig. 2. Output Characteristics at 125°C

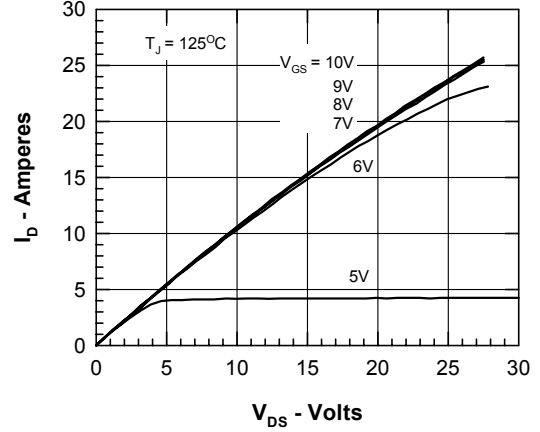


Fig. 3.  $R_{DS(ON)}$  vs. Drain Current

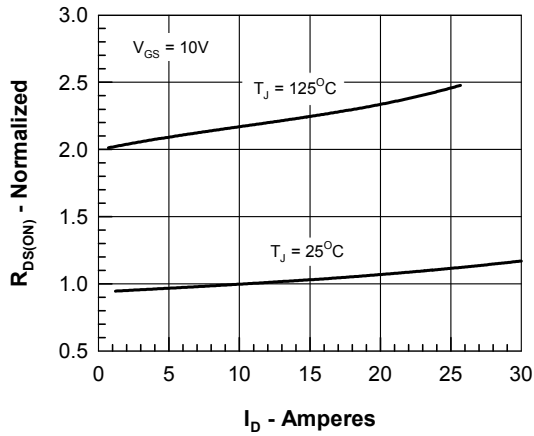


Fig. 4.  $R_{DS(ON)}$  vs.  $T_J$

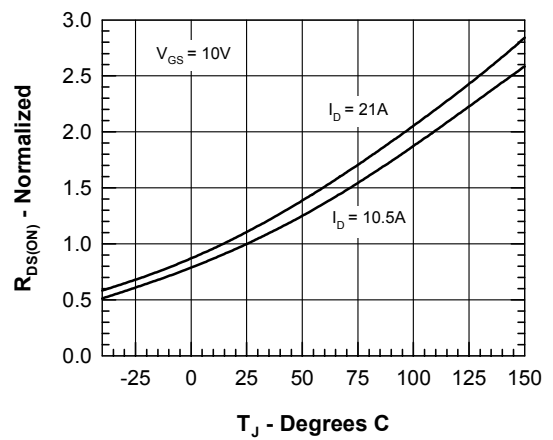


Fig. 5. Drain Current vs. Case Temperature

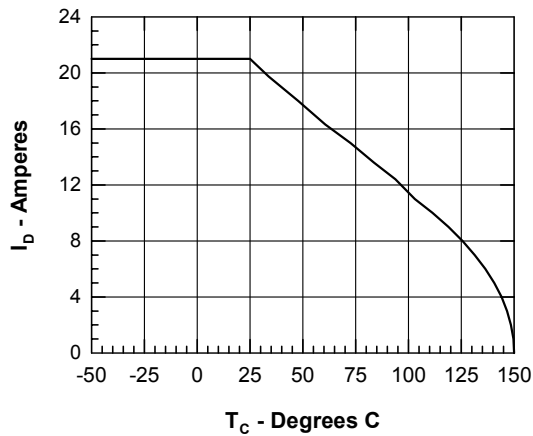


Fig. 6. Admittance Curves

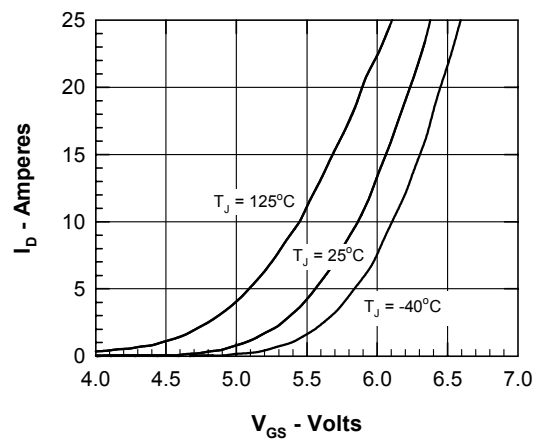


Fig. 7. Gate Charge Characteristic Curve

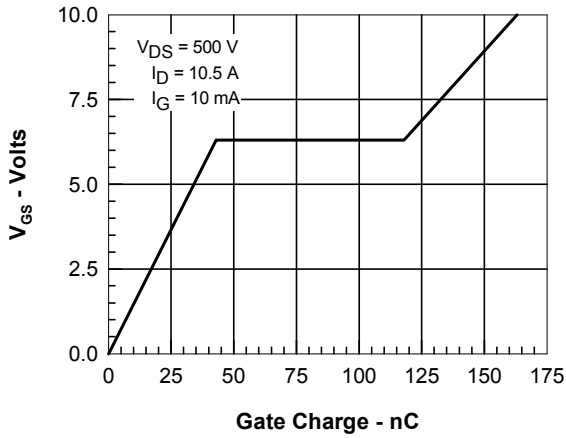


Fig. 8. Capacitance Curves

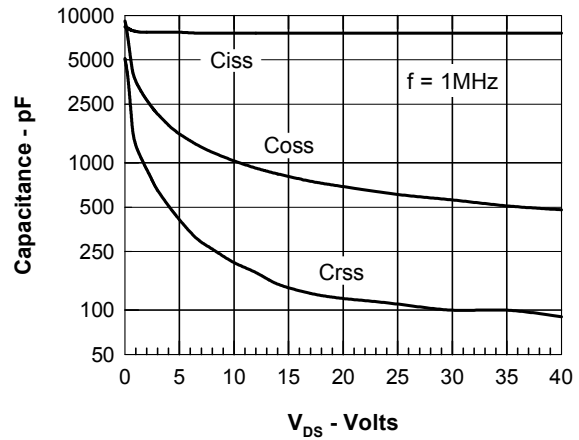


Fig. 9. Source Current vs. Source to Drain Voltage

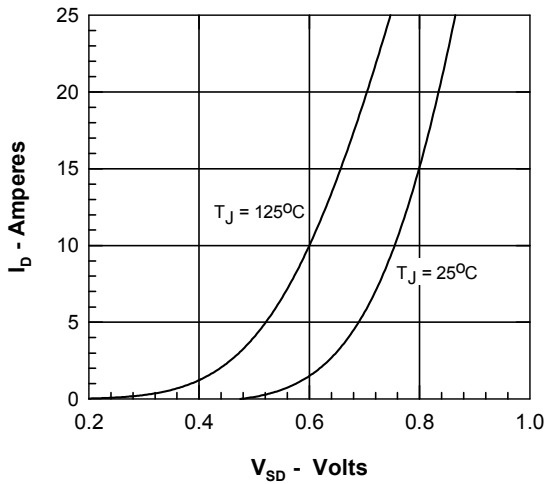


Fig. 10. Thermal Impedance

